

U.S. DEPARTMENT OF COMMERCE
 PATENT AND TRADEMARK OFFICE

**INFORMATION DISCLOSURE
 STATEMENT**

Docket Number:
10191/3939

Application Number
To be assigned

Filing Date
Herewith

Examiner
To be assigned

Art Unit
To be assigned

Invention Title
**A LAYER SYSTEM COMPRISING A SILICON
 LAYER AND A PASSIVATING LAYER, A
 METHOD FOR PRODUCING A PASSIVATING
 LAYER ON A SILICON LAYER AND THEIR
 USE**

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 Commissioner For Patents
 Alexandria, VA 22313-1450

1. In accordance with the duty of disclosure under 37 C.F.R. § 1.56 and in conformance with the procedures of 37 C.F.R. §§ 1.97 and 1.98 and M.P.E.P. § 609, attorneys for Applicants hereby bring the following references to the attention of the Examiner. The references are listed on the attached modified PTO Form No. 1449. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.
2. A copy of the patents listed on the modified PTO form 1449 are enclosed, unless otherwise indicated.

Dated: 1/10/05

By: 
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p. no.
 36,197

INFORMATION DISCLOSURE STATEMENT BY APPLICANT PTO-1449	DOCKET NO. 10191/3939	SEQUENCE NO. 10/520886 To be assigned
	APPLICANT Andrea URBAN et al.	
	FILING DATE To be assigned	GROUP To be assigned

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT/PUBLICATION NUMBER	PATENT/PUBLICATION DATE	NAME	CLASS	SUBCLASS	FILING DATE
	* 4,576,834	March 18, 1986	SOBCZAK, Z. P.			
	* 5,116,460	May 26, 1992	BUKHMANN, Y.			

* Copy of reference is not enclosed because reference is cited and described in Search Report (copy of reference provided by the International Searching Authority).

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						Yes	No
	199 19 469	November 2, 2000	DE			X*	
	42 41 045	June 16, 1994	DE			X**	
	44 20 962	December 21, 1995	DE			X**	
	198 47 455	April 27, 2000	DE			X**	
	197 06 682	August 27, 1998	DE			X**	
	199 00 179	February 24, 2000	DE			X**	

* Copy of reference is not enclosed because reference is cited and described in Search Report (copy of reference provided by the International Searching Authority).

** Mentioned in Specification.

OTHER DOCUMENTS

EXAMINER INITIAL	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
	* Ohara, J; Kano, K.; Takeuchi, Y.; Ohya, N.; Otsuka, Y.; Akita, S.: "A new deep reactive ion etching process by dual sidewall protection," Proceeding IEEE Thirteenth Annual International Conference On Micro Electro Mechanical Systems, Miyazaki, Japan, 23 - 27 January 2000, pp. 277-282.

* Copy of reference is not enclosed because reference is cited and described in Search Report (copy of reference provided by the International Searching Authority).

EXAMINER	DATE CONSIDERED
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	